

(Note 1c)

(Note 1)

© 1998 Fairchild Semiconductor Corporation

THERMAL CHARACTERISTICS

Operating and Storage Temperature Range

Thermal Resistance, Junction-to-Case

Thermal Resistance, Junction-to-Ambient (Note 1a)

T_J,T_{STG}

 $\mathsf{R}_{\theta \mathsf{JC}}$

°C

°C/W

°C/W

1

-55 to 150

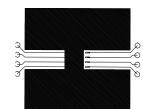
50

25

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS				•	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	30			V
$\Delta BV_{DSS} / \Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_{\rm D}$ = 250 µA, Referenced to 25 °C		21		mV /°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 V, V_{GS} = 0 V$			1	μA
		$T_{J} = 55^{\circ}C$			10	μA
	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
ON CHARA	CTERISTICS (Note 2)				•	•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	2	3	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate Threshold Voltage Temp. Coefficient	$I_{\rm D}$ = 250 µA, Referenced to 25 °C		-4.5		mV /°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		0.011	0.0135	Ω
		T _J =125°C		0.018	0.023	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 9 \text{ A}$		0.017	0.02	
I _{D(ON)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	50			Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		27		S
DYNAMIC C	CHARACTERISTICS					
C _{iss}	Input Capacitance	$V_{DS} = 15 V, V_{GS} = 0 V,$ f = 1.0 MHz		1340		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		340		pF
C _{rss}	Reverse Transfer Capacitance			125		pF
SWITCHING	CHARACTERISTICS (Note 2)					
t _{D(on)}	Turn - On Delay Time	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 1 \text{ A}$		12	22	ns
t,	Turn - On Rise Time	$V_{\text{GS}} = 10 \text{ V} \text{ , } \text{ R}_{\text{GEN}} = 6 \Omega$		13	24	ns
t _{D(off)}	Turn - Off Delay Time			38	60	ns
t,	Turn - Off Fall Time			10	18	ns
Q _g	Total Gate Charge	$V_{DS} = 15 \text{ V}, \ I_{D} = 10 \text{ A},$		22	31	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		5		nC
Q _{gd}	Gate-Drain Charge			4		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MAXIM	UM RATINGS				
I _s	Maximum Continuous Drain-Source Diode Forward Current				2.1	Α
V _{SD}	Drain-Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_S = 2.1 \text{ A}$ (Note 2)			0.73	1.2	V

Notes:

1. R_{gat} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{gat} is guaranteed by design while $R_{\mbox{\tiny BCA}}$ is determined by the user's board design.





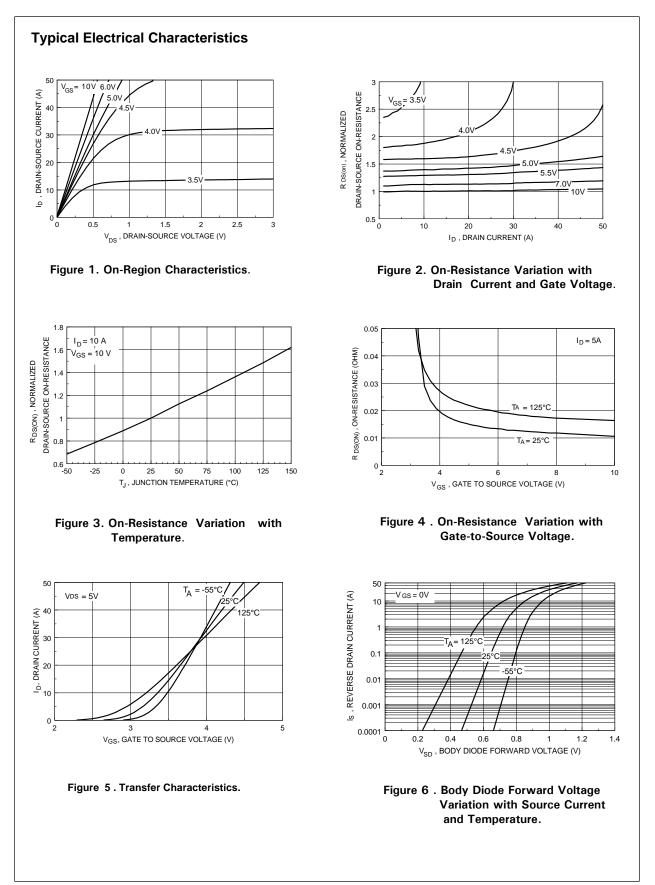


b. 105°C/W on a 0.04 in² pad of 2oz copper.

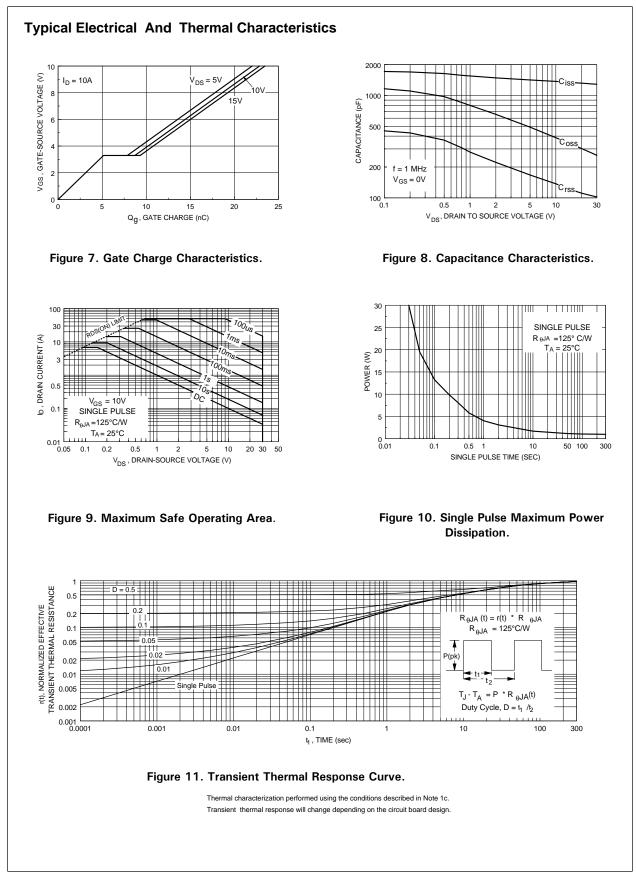


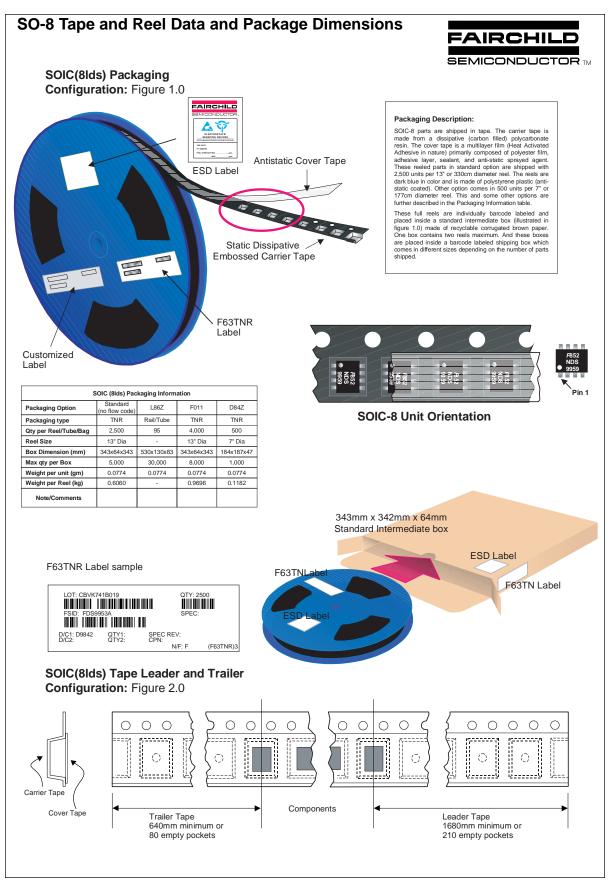
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

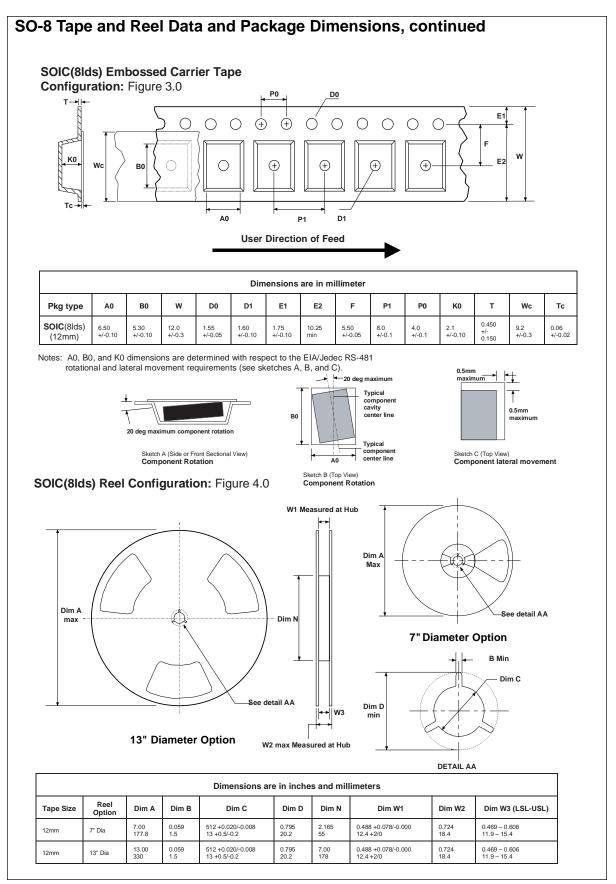


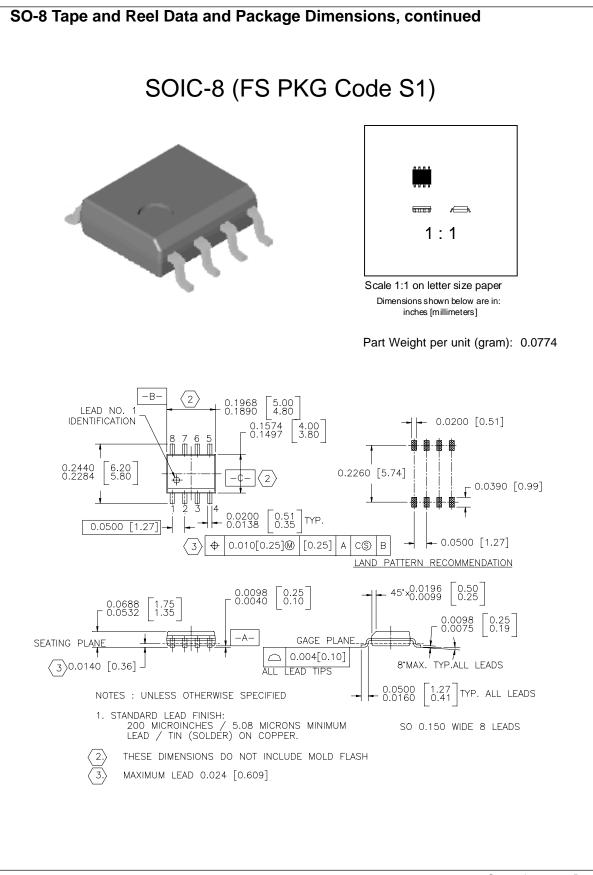
FDS4410 Rev.B1





July 1999, Rev. B





TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACExTM CoolFETTM CROSSVOLTTM E²CMOSTM FACTTM FACT Quiet SeriesTM FAST[®] FAST[®] FASTrTM GTOTM HiSeCTM ISOPLANAR[™] MICROWIRE[™] POP[™] PowerTrench[™] QFET[™] QS[™] Quiet Series[™] SuperSOT[™]-3 SuperSOT[™]-6 SuperSOT[™]-8

TinyLogic™ UHC™ VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition	
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.	
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.	
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.	
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconduct The datasheet is printed for reference information or	